

(a) (b) (c)	A crystal diode has one pn junction two pn junctions three pn junctions none of the above
2.	A crystal diode has forward resistance of the order of
3.	If the arrow of crystal diode symbol is positive w.r.t. bar, then diode is biased. (a) forward (b) reverse (c) either forward or reverse (d) none of the above
4.	The reverse current in a diode is of the order of
5.	The forward voltage drop across a silicon diode is about
6.	A crystal diode is used as



	(a) an amplifier(b)a rectifier(c) an oscillator(d) a voltage regulator
7.	An ideal crystal diode is one which behaves as a perfect when forward biased. (a) conductor (b) insulator (c) resistance material (d) none of the above
8.	The leakage current in a crystal diode is due to
9.	If the temperature of a crystal diode increases, then leakage current
10	.If the doping level of a crystal diode is increased, the breakdown voltage (a) remains the same (b) is increased (c) is decreased (d) none of the above
11	.The knee voltage of a crystal diode is approximately equal to



(a) applied voltage(b) breakdown voltage(c) forward voltage(d) barrier potential	
12.A crystal diode is a device (a) non-linear (b) bilateral (c) linear (d) none of the above	
13.A zener diode is used as	
14.A zener diode is always connected. (a) reverse (b) forward (c) either reverse or forward (d) none of the above	
 15. The electrical resistance of the depletion layer is large because (a) It has no change carriers (b) It has a large number of charge carriers (c) It contains electrons as charge carriers (d) It has holes as charge carriers 	
16. When a PN junction diode is reverse biased (a) Electrons and holes are attracted towards each other and move towards	ds

the depletion region



(b)Electrons	and holes	move awa	v from 1	the i	iunction	depletion	region
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- (c) Height of the potential barrier decreases
- (d) No change in the current takes place

17.On increasing the revers	se bias to	a large	value i	n a PN	junction	diode,
current						

- (a) Increases slowly
- (b) Remains fixed
- (c) Suddenly increases
- (d) Decreases slowly

18	Which	of th	e foll	owing	are t	he	charge	carriers	availa	hle	in	RIT?
10	. * * 111011	or u	ic rom	OWINE	arc t	uic '	Charge	carriers	avanc	ioic	111	DJI:

- (a) Holes
- (b) Electrons
- (c) Neutrons
- (d) Both a and b

19.How many	terminals do	a BJT have?
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- (a) 1
- (b) 2
- (c) 3
- (d) 4

20. Which of the following BJT terminal controls the current flow?

- (a) Base
- (b) Collector
- (c) Emitter
- (d) All of the above

21. Which of the following terminals of BJT are slightly doped?

- (a) Base
- (b) Collector



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(c) Emitter	
(d) Both b and c	
22. Which of the following terminals of BJT are heavily doped?	
(a) Base	
(b) Collector	
(c) Emitter	
(d) Both b and c	
23. Which of the following terminals of BJT is extremely thin?	
(a) Base	
(b) Collector	
(c) Emitter	
(d) Both b and c	
24. The arrow in BJT symbol represents	
(a) Flow of current	
(b) Flow of resistance	
(c) Direction of current	
(d) Both a and c	
(a) Both a and c	
25. Which of the following BJT region does amplification?	
(a) Active	
(b) Cut-off	
(c) Saturation	

26. Which of the following region in BJT is an linear region?

(d) Both a and c

(a) Active(b) Cut-off(c) Saturation(d) Both a and c



 27. Which of the following region in BJT is an non-linear region? (a) Active (b) Cut-off (c) Saturation (d) Both b and c
 28. Which of the following BJT region perform switching? (a) Active (b) Cut-off (c) Saturation (d) Both b and c
 29. Which of the following terminal is grounded in common base configuration of BJT? (a) Base (b) Emitter (c) Collector (d) Drain
 30. Which of the following terminal is grounded in common emitter configuration of BJT? (a) Base (b) Emitter (c) Collector (d) Drain
31. What is gain value of common base BJT? (a) = 1 (b) <1 (c) >1 (d) 0



32. The equation of emitter current of BJT?
(a) Ie=Ic+Ib
(b) Ie=Ic-Ib
(c) Ie=Ic/Ib
(d) Ie=Ic*Ib
33. The value of input impedance of common emitter configuration of BJT is
?
(a) High
(b) Low
(c) Medium
(d) Zero
34. The value of output impedance of common emitter configuration of BJT is
?
(a) High
(b) Low
(c) Medium
(d) Zero
25 The value of phase and of CE is
35.The value of phase angle of CE is? (a) 0
(a) 6 (b) 180
(c) 90
(d) 45
36.The value of current gain of common emitter BJT is?
(a) High
(b) Low
(c) Medium
(d) Zero



37. The value of current gain of common base BJT is? (a) High (b) Low (c) Medium (d) Zero
 38.What does MOSFET stands for? (a) Metal Oxide Semiconductor Field Effect Transistor (b) Modern Oxidized Silicon based Field Effect Transistor (c) Modern Oxidized Silicon based Force Effect Transistor (d) Metal Oxide silicon Field Equivalent Transistor
 39.What type of a device is MOSFET? (a) Current-controlled (b) Voltage-controlled (c) Voltage-controlled Current source (d) Voltage-controlled Voltage source
40.How many terminals does a MOSFET possess?(a) One(b) Two(c) Three(d) Four
41. Which transistor is preferred for applications of High power? (a) BJT (b) UJT (c) MOSFET (d) JFET



(a) JFET (b) UJT
(b) UJT
(c) MOSFET
(d) CMOS
43.Depletion mode MOSFETs can operate in mode.
(a) Enhancement
(b) Depletion
(c) Enhancement and Depletion
(d) none of the above
44.MOSFET is
(a) Unidirectional
(b) Bidirectional
(c) Unipolar
(d) b & c
45. CMOS stands for
(a) Complementary Metal Oxide Semiconductor
(b) Commutative Metal Oxide Semiconductor
(c) Cosmopolitan MOS
(d) Customize MOS
46. When no ac input signals are connected to CE Transistor, Load line can be
plotted
(a) V_{CE} V_{S} V_{CC}
$(b) V_{CE} V_{S} I_{E}$
$(c) V_{CE} Vs I_{C}$
$(d) V_{BE} V_{S} I_{B}$

47. Operating point of a transistor amplifier is known as

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a.	Saturation point	
b.	Quiescent point	
c.	Cut-off point	
d.	Flood in point	
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- 48. In how many regions can a biased transistor work?
 - a. One
 - b. Two
 - c. Three
 - d. Four
- 49. Which of the following method of biasing provides the best operating point stability?
 - a. Fixed resistor bias
 - b. Collector to base bias
 - c. Emitter bias
 - d. Self bias
- 50. Transistor biasing is done to keepin the circuit
 - a. Proper direct current
 - b. Proper alternating current
 - c. Base current small
 - d. Collector current small